

Takeshi Yoshimura

List of Publications by Year in descending order

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papers

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194
all docs

194
docs citations

194
times ranked

1737
citing authors

#	ARTICLE	IF	CITATIONS
1	Epitaxially grown YMnO ₃ film: New candidate for nonvolatile memory devices. Applied Physics Letters, 1996, 69, 1011-1013.	1.5	303
2	Ferroelectric properties of YMnO ₃ epitaxial films for ferroelectric-gate field-effect transistors. Journal of Applied Physics, 2003, 93, 5563-5567.	1.1	105
3	Growth mechanism of YMnO ₃ film as a new candidate for nonvolatile memory devices. Journal of Applied Physics, 1996, 80, 7084-7088.	1.1	94
4	Characterization of ferroelectricity in metal/ferroelectric/insulator/semiconductor structure by pulsed C-V measurement; Ferroelectricity in YMnO ₃ /Y ₂ O ₃ /Si structure. Journal of Applied Physics, 2000, 87, 3444-3449.	1.1	72
5	Direct piezoelectric properties of (100) and (111) BiFeO ₃ epitaxial thin films. Applied Physics Letters, 2012, 100, 102901.	1.5	69
6	Ferroelectric properties of c-oriented YMnO ₃ films deposited on Si substrates. Applied Physics Letters, 1998, 73, 414-416.	1.5	60
7	Raman scattering studies on multiferroic YMnO ₃ . Journal of Physics Condensed Matter, 2007, 19, 365239.	0.7	55
8	Growth and properties of (001) BiScO ₃ -PbTiO ₃ epitaxial films. Applied Physics Letters, 2002, 81, 2065-2066.	1.5	54
9	Ferromagnetic and ferroelectric behaviors of A-site substituted YMnO ₃ -based epitaxial thin films. Journal of Applied Physics, 2003, 93, 6990-6992.	1.1	44
10	YMnO ₃ Thin Films Prepared from Solutions for Non Volatile Memory Devices. Japanese Journal of Applied Physics, 1997, 36, L1601-L1603.	0.8	41
11	Piezoelectric Vibrational Energy Harvester Using Lead-Free Ferroelectric BiFeO ₃ Films. Applied Physics Express, 2013, 6, 051501.	1.1	37
12	Electrical Characteristics of Controlled-Polarization-Type Ferroelectric-Gate Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8874.	0.8	35
13	Influence of Schottky and Poole-Frenkel emission on the retention property of YMnO ₃ -based metal/ferroelectric/insulator/semiconductor capacitors. Journal of Applied Physics, 2003, 94, 4036-4041.	1.1	34
14	Influence of antiferromagnetic exchange interaction on magnetic properties of ZnMnO thin films grown pseudomorphically on ZnO (0001 \bar{A}) single-crystal substrates. Journal of Applied Physics, 2008, 103, .	1.1	33
15	Pulsed-Laser-Deposited YMnO ₃ Epitaxial Films with Square Polarization-Electric Field Hysteresis Loop and Low-Temperature Growth. Japanese Journal of Applied Physics, 2004, 43, 6613-6616.	0.8	31
16	Systematic Study of Photoluminescence Enhancement in Monolayer Molybdenum Disulfide by Acid Treatment. Langmuir, 2018, 34, 10243-10249.	1.6	29
17	Epitaxial growth of CuScO ₂ thin films on sapphire a-plane substrates by pulsed laser deposition. Journal of Applied Physics, 2005, 97, 083535.	1.1	25
18	Direct Piezoelectric Properties of Mn-Doped ZnO Epitaxial Films. Japanese Journal of Applied Physics, 2010, 49, 021501.	0.8	25

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19	The initial stage of BaTiO ₃ epitaxial films on etched and annealed SrTiO ₃ substrates. Journal of Crystal Growth, 1997, 174, 790-795.	0.7	24
20	Photoactivation of Strong Photoluminescence in Superacid-Treated Monolayer Molybdenum Disulfide. ACS Applied Materials & Interfaces, 2020, 12, 36496-36504.	4.0	24
21	Growth and piezoelectric properties of Pb(Yb _{1/2} Nb _{1/2})O ₃ ~PbTiO ₃ epitaxial films. Journal of Applied Physics, 2002, 92, 3979-3984.	1.1	23
22	Transverse piezoelectric properties of epitaxial Pb(Yb _{1/2} Nb _{1/2})O ₃ ~PbTiO ₃ (50/50) films. Journal of Crystal Growth, 2001, 229, 445-449.	0.7	22
23	Fabrication of YMnO ₃ Thin Films on Si Substrates by a Pulsed Laser Deposition Method. Japanese Journal of Applied Physics, 1997, 36, 5921-5924.	0.8	21
24	Effect of Mn doping on the electric and dielectric properties of ZnO epitaxial films. Journal of Applied Physics, 2008, 103, .	1.1	21
25	Single-Wall Carbon Nanotube Field Effect Transistors with Non-Volatile Memory Operation. Japanese Journal of Applied Physics, 2006, 45, L1036-L1038.	0.8	20
26	Multiferroic behaviour of YMnO ₃ and YbMnO ₃ epitaxial films. Philosophical Magazine Letters, 2007, 87, 193-201.	0.5	20
27	Dielectric and transverse piezoelectric properties of sol-gel-derived (001) Pb[Yb _{1/2} Nb _{1/2}]O ₃ ~PbTiO ₃ epitaxial thin films. Applied Physics Letters, 2003, 82, 4767-4769.	1.5	19
28	Analysis of nitrogen plasma generated by a pulsed plasma system near atmospheric pressure. Journal of Applied Physics, 2004, 96, 6094-6096.	1.1	19
29	Development of Piezoelectric MEMS Vibration Energy Harvester Using (100) Oriented BiFeO ₃ Ferroelectric Film. Journal of Physics: Conference Series, 2013, 476, 012007.	0.3	19
30	Enhancement of piezoelectric properties of (100)-orientated BiFeO ₃ films on (100)LaNiO ₃ /Si. Japanese Journal of Applied Physics, 2014, 53, 09PA14.	0.8	19
31	Thickness dependence of piezoelectric properties of BiFeO ₃ films fabricated using rf magnetron sputtering system. Japanese Journal of Applied Physics, 2016, 55, 10TA16.	0.8	19
32	Demonstration of high-performance piezoelectric MEMS vibration energy harvester using BiFeO ₃ film with improved electromechanical coupling factor. Sensors and Actuators A: Physical, 2019, 291, 167-173.	2.0	19
33	Spin~phonon coupling in multiferroic YbMnO ₃ studied by Raman scattering. Journal of Physics Condensed Matter, 2009, 21, 064218.	0.7	18
34	Time~Dependent Imprint in Hf _{0.5} Zr _{0.5} O ₂ Ferroelectric Thin Films. Advanced Electronic Materials, 2021, 7, 2100151.	2.6	18
35	Effects of Stoichiometry and A-site Substitution on the Electrical Properties of Ferroelectric YMnO ₃ . Japanese Journal of Applied Physics, 1998, 37, 5280-5284.	0.8	17
36	Optical and electrical properties of CuScO ₂ epitaxial films prepared by combining two-step deposition and post-annealing techniques. Journal of Crystal Growth, 2009, 311, 1117-1122.	0.7	17

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37	Reaction of Si with excited nitrogen species in pure nitrogen plasma near atmospheric pressure. Thin Solid Films, 2006, 506-507, 423-426.	0.8	16
38	Preparation and the magnetic property of ZnMnO thin films on ZnO single crystal substrate. Journal of Magnetism and Magnetic Materials, 2007, 310, e711-e713.	1.0	15
39	Electromechanical characteristics of piezoelectric vibration energy harvester with 2-degree-of-freedom system. Applied Physics Letters, 2019, 114, .	1.5	15
40	Improvement of Y2O3/Si interface for FeRAM application. Applied Surface Science, 2000, 159-160, 138-142.	3.1	14
41	Detailed structural analysis and dielectric properties of silicon nitride film fabricated using pure nitrogen plasma generated near atmospheric pressure. Journal of Applied Physics, 2006, 100, 073710.	1.1	14
42	Analysis of carrier modulation in channel of ferroelectric-gate transistors having polar semiconductor. Thin Solid Films, 2010, 518, 3026-3029.	0.8	14
43	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	0.8	14
44	Effect of Ferroelectric Polarization Domain Structure on Electronic Transport Property of Ferroelectric/ZnO Heterostructure. Japanese Journal of Applied Physics, 2011, 50, 09NA06.	0.8	14
45	Polarization Hysteresis Loops of Ferroelectric Gate Capacitors Measured by Sawyer-Tower Circuit. Japanese Journal of Applied Physics, 2003, 42, 6011-6014.	0.8	13
46	Synthesis of Bi(FexAl1-x)O3 Thin Films by Pulsed Laser Deposition and Its Structural Characterization. Japanese Journal of Applied Physics, 2004, 43, 6609-6612.	0.8	13
47	Effect of electrically degenerated layer on the carrier transport property of ZnO epitaxial thin films. Applied Surface Science, 2008, 254, 6248-6251.	3.1	13
48	Growth and Ferromagnetic Properties of Ferroelectric YbMnO3 Thin Films. Japanese Journal of Applied Physics, 2006, 45, 7329-7331.	0.8	12
49	Spin-coupled phonons in multiferroic YbMnO ₃ epitaxial films by Raman scattering. Journal of Physics: Conference Series, 2007, 92, 012126.	0.3	12
50	Magnetic frustration behavior of ferroelectric ferromagnet YbMnO3 epitaxial films. Journal of Applied Physics, 2007, 101, 09M107.	1.1	12
51	Effects of Oxygen Annealing on Dielectric Properties of LuFeCuO ₄ . Japanese Journal of Applied Physics, 2008, 47, 8464.	0.8	12
52	Polarization Switching Behavior of YMnO ₃ Thin Film at around Magnetic Phase Transition Temperature. Japanese Journal of Applied Physics, 2009, 48, 09KB05.	0.8	12
53	Development of piezoelectric bistable energy harvester based on buckled beam with axially constrained end condition for human motion. Japanese Journal of Applied Physics, 2017, 56, 10PD02.	0.8	12
54	Formation of YMnO3 films directly on Si substrate. Journal of Crystal Growth, 1997, 174, 796-800.	0.7	11

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55	Electrical and optical properties of excess oxygen intercalated CuScO ₂ (0001) epitaxial films prepared by oxygen radical annealing. <i>Thin Solid Films</i> , 2008, 516, 5785-5789.	0.8	11
56	Effects of Mg doping on structural, optical, and electrical properties of CuScO ₂ (0001) epitaxial films. <i>Vacuum</i> , 2009, 84, 618-621.	1.6	11
57	Local Piezoelectric and Conduction Properties of BiFeO ₃ Epitaxial Thin Films. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 09MB02.	0.8	11
58	Piezoelectric properties of (100) orientated BiFeO ₃ thin films on LaNiO ₃ . <i>Japanese Journal of Applied Physics</i> , 2014, 53, 08NB02.	0.8	11
59	Magnetic properties of low-temperature grown Si:Ce thin films on (001) Si substrate. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 310, e726-e728.	1.0	10
60	Contribution of s-d exchange interaction to magnetoresistance of ZnO-based heterostructures with a magnetic barrier. <i>Physical Review B</i> , 2009, 80, .	1.1	10
61	Fine-structured patterns of porous alumina material fabricated by a replication method. <i>Journal of the European Ceramic Society</i> , 2010, 30, 2735-2739.	2.8	10
62	Control of cathodic potential for deposition of ZnO by constant-current electrochemical method. <i>Thin Solid Films</i> , 2010, 518, 2957-2960.	0.8	10
63	Enhancement of Direct Piezoelectric Properties of Domain-Engineered (100) BiFeO ₃ Films. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 09KA03.	0.8	10
64	Correlation between the intra-atomic Mn ³⁺ photoluminescence and antiferromagnetic transition in an YMnO ₃ epitaxial film. <i>Applied Physics Express</i> , 2014, 7, 023002.	1.1	10
65	Piezoelectric energy harvesting from AC current-carrying wire. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLD10.	0.8	10
66	Characterization of Direct Piezoelectric Properties for Vibration Energy Harvesting. <i>IOP Conference Series: Materials Science and Engineering</i> , 2011, 18, 092026.	0.3	9
67	Lowering the growth temperature of strongly-correlated YbFe ₂ O ₄ thin films prepared by pulsed laser deposition. <i>Thin Solid Films</i> , 2016, 614, 44-46.	0.8	9
68	Investigation of mechanical nonlinear effect in piezoelectric MEMS vibration energy harvesters. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 11UD03.	0.8	9
69	Direct Piezoelectricity of PZT Films and Application to Vibration Energy Harvesting. <i>Journal of the Korean Physical Society</i> , 2011, 59, 2524-2527.	0.3	9
70	Low-Temperature Growth and Characterization of Epitaxial YMnO ₃ /Y ₂ O ₃ /Si MFIS Capacitors with Thinner Insulator Layer. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 6977-6980.	0.8	8
71	Growth process observation of homoepitaxial ZnO thin films using optical emission spectra during pulsed laser deposition. <i>Thin Solid Films</i> , 2010, 518, 2971-2974.	0.8	8
72	Characterization of Direct Piezoelectric Effect in 31 and 33 Modes for Application to Vibration Energy Harvester. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 09ND17.	0.8	8

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73	Control of Crystal Structure of BiFeO ₃ Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. Japanese Journal of Applied Physics, 2012, 51, 09LB04.	0.8	8
74	Crystal structure and local piezoelectric properties of strain-controlled (001) BiFeO ₃ epitaxial thin films. Thin Solid Films, 2014, 550, 738-741.	0.8	8
75	The effects of small amounts of oxygen during deposition on structural changes in sputtered HfO ₂ -based films. Japanese Journal of Applied Physics, 2019, 58, SLLB03.	0.8	8
76	Good piezoelectricity of self-polarized thick epitaxial (K,Na)NbO ₃ films grown below the Curie temperature (240°C) using a hydrothermal method. Applied Physics Letters, 2020, 117, .	1.5	8
77	Ultralarge Photoluminescence Enhancement of Monolayer Molybdenum Disulfide by Spontaneous Superacid Nanolayer Formation. ACS Applied Materials & Interfaces, 2021, 13, 25280-25289.	4.0	8
78	Formation of Silicon Oxynitride Films with Low Leakage Current Using N ₂ /O ₂ Plasma near Atmospheric Pressure. Japanese Journal of Applied Physics, 2004, 43, 7853-7856.	0.8	7
79	Spin-dependent transport in a ZnMnO ₂ /ZnO heterostructure. Journal of Applied Physics, 2008, 103, 07D124.	1.1	7
80	Magnetic Properties of Uniformly Ce-Doped Si Thin Films with n-Type Conduction. Japanese Journal of Applied Physics, 2009, 48, 033003.	0.8	7
81	Surface preparation of ZnO single-crystal substrate for the epitaxial growth of ZnO thin films. Journal of Crystal Growth, 2011, 318, 516-518.	0.7	7
82	Effect of Al-doped ZnO or Sn-doped In ₂ O ₃ electrode on ferroelectric properties of (Pb,La)(Zr,Ti)O ₃ capacitors. Japanese Journal of Applied Physics, 2015, 54, 05ED03.	0.8	7
83	Evaluation of the electronic states in highly Ce doped Si films grown by low temperature molecular beam epitaxy system. Journal of Crystal Growth, 2015, 425, 158-161.	0.7	7
84	Direct measurements of electrocaloric effect in ferroelectrics using thin-film thermocouples. Japanese Journal of Applied Physics, 2016, 55, 10TB04.	0.8	7
85	Growth and ferroelectric properties of La and Al codoped BiFeO ₃ epitaxial films. Journal of Applied Physics, 2017, 121, 174102.	1.1	7
86	Control of native acceptor density in epitaxial Cu ₂ O thin films grown by electrochemical deposition. Journal of Crystal Growth, 2017, 468, 245-248.	0.7	7
87	Effect of Additional Oxygen on Formation of Silicon Oxynitride Using Nitrogen Plasma Generated near Atmospheric Pressure. Japanese Journal of Applied Physics, 2006, 45, 9025-9028.	0.8	6
88	Influence of antiferromagnetic ordering on ferroelectric polarization switching of YMnO ₃ /epitaxial thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2007, 54, 2641-2644.	1.7	6
89	The comparison of the growth models of silicon nitride ultrathin films fabricated using atmospheric pressure plasma and radio frequency plasma. Journal of Applied Physics, 2007, 101, 023513.	1.1	6
90	Electron transport properties of Zn _{0.88} Mn _{0.12} O ₂ /ZnO modulation-doped heterostructures. Journal of Vacuum Science & Technology B, 2009, 27, 1760.	1.3	6

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91	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	0.8	6
92	Effect of the annealing temperature of P(VDF/TrFE) thin films on their ferroelectric properties. Journal of the Korean Physical Society, 2013, 62, 1065-1068.	0.3	6
93	Effect of excess Pb on ferroelectric characteristics of conductive Al-doped ZnO and Sn-doped In ₂ O ₃ top electrodes in PbLaZrTiO _x capacitors. International Journal of Materials Research, 2015, 106, 83-87.	0.1	6
94	Comparative Study of Hydrogen- and Deuterium-Induced Degradation of Ferroelectric (Pb,La)(Zr,Ti)O ₃ Capacitors Using Time-of-Flight Secondary Ion Measurement. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2016, 63, 1668-1673.	1.7	6
95	Convection-Flow-Assisted Preparation of a Strong Electron Dopant, Benzyl Viologen, for Surface-Charge Transfer Doping of Molybdenum Disulfide. ChemistryOpen, 2019, 8, 908-914.	0.9	6
96	Investigation of the wake-up process and time-dependent imprint of Hf _{0.5} Zr _{0.5} O ₂ film through the direct piezoelectric response. Applied Physics Letters, 2021, 119, .	1.5	6
97	Investigation of efficient piezoelectric energy harvesting from impulsive force. Japanese Journal of Applied Physics, 2020, 59, SPPD04.	0.8	6
98	Electronic Transport Property of a YbMnO ₃ /ZnO Heterostructure. Journal of the Korean Physical Society, 2011, 58, 792-796.	0.3	6
99	Effect of Ferroelectric Polarization on Carrier Transport in Controlled Polarization-Type Ferroelectric Gate Field-Effect Transistors with Poly(vinylidene fluoride-tetrafluoroethylene)/ZnO Heterostructure. Japanese Journal of Applied Physics, 2012, 51, 11PB01.	0.8	6
100	Phase Development and Electrical Properties of Pb(Yb 1/2 Nb 1/2)O ₃ -PbTiO ₃ Epitaxial Films. Integrated Ferroelectrics, 2002, 50, 33-42.	0.3	5
101	Novel Ferroelectric Gate Thin-Film Transistors Using a Polar Semiconductor Channel. Japanese Journal of Applied Physics, 2006, 45, L1266-L1269.	0.8	5
102	Dielectric properties of ferroelectric/DMS heterointerface using YMnO ₃ and Ce doped Si. Applied Surface Science, 2008, 254, 6218-6221.	3.1	5
103	Control of carrier concentration of p-type transparent conducting CuScO ₂ (0001) epitaxial films. Thin Solid Films, 2010, 518, 3097-3100.	0.8	5
104	Effect of Ferroelectric Polarization Domain Structure on Electronic Transport Property of Ferroelectric/ZnO Heterostructure. Japanese Journal of Applied Physics, 2011, 50, 09NA06.	0.8	5
105	Effect of Target Surface Microstructure on Morphological and Electrical Properties of Pulsed-Laser-Deposited BiFeO ₃ Epitaxial Thin Films. Japanese Journal of Applied Physics, 2013, 52, 045803.	0.8	5
106	Aluminum-doped zinc oxide electrode for robust (Pb,La)(Zr,Ti)O ₃ capacitors: effect of oxide insulator encapsulation and oxide buffer layer. Journal of Materials Science: Materials in Electronics, 2014, 25, 2155-2161.	1.1	5
107	Theoretical analysis of linear and nonlinear piezoelectric vibrational energy harvesters for human walking. Japanese Journal of Applied Physics, 2015, 54, 10ND02.	0.8	5
108	Al:ZnO top electrodes deposited with various oxygen pressures for ferroelectric (Pb,La)(Zr,Ti)O ₃ capacitors. Electronics Letters, 2016, 52, 230-232.	0.5	5

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109	Low-voltage operation of Si-based ferroelectric field effect transistors using organic ferroelectrics, poly(vinylidene fluoride-trifluoroethylene), as a gate dielectric. Japanese Journal of Applied Physics, 2016, 55, 04EE04.	0.8	5
110	Photoelectron spectroscopic study on monolayer pentacene thin-film/polar ZnO single-crystal hybrid interface. Applied Physics Express, 2017, 10, 025702.	1.1	5
111	The effect of crystal distortion and domain structure on piezoelectric properties of BiFeO ₃ thin films. Japanese Journal of Applied Physics, 2018, 57, 11UF07.	0.8	5
112	Direct piezoelectric properties of BiFeO ₃ epitaxial films grown by combinatorial sputtering. Journal of Physics: Conference Series, 2018, 1052, 012020.	0.3	5
113	Solvent engineering for strong photoluminescence enhancement of monolayer molybdenum disulfide in redox-active molecular treatment. Applied Physics Express, 2019, 12, 051014.	1.1	5
114	Investigation of the electrocaloric effect in ferroelectric polymer film through direct measurement under alternating electric field. Applied Physics Express, 2020, 13, 041007.	1.1	5
115	Low Temperature Growth of ZnO Thin Films by Non-Equilibrium Atmospheric Pressure N ₂ /O ₂ Plasma and the Growth Morphology of the Films. Zairyo/Journal of the Society of Materials Science, Japan, 2012, 61, 756-759.	0.1	5
116	Control of Crystal Structure of BiFeO ₃ Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. Japanese Journal of Applied Physics, 2012, 51, 09LB04.	0.8	5
117	Improvement of Surface Morphology and Dielectric Property of YMnO ₃ Films. Japanese Journal of Applied Physics, 2003, 42, 6003-6006.	0.8	4
118	Fabrication of the fine structured alumina materials with nanoimprint method. Journal of the Ceramic Society of Japan, 2009, 117, 534-536.	0.5	4
119	Fine-structured ZnO patterns with sub-micrometer on the ceramic surface fabricated by a replication method. Journal of the Ceramic Society of Japan, 2010, 118, 1140-1143.	0.5	4
120	Investigation of Gas Sensing Characteristics of TiO ₂ Nanotube Field-Effect Transistor. Japanese Journal of Applied Physics, 2012, 51, 11PE10.	0.8	4
121	Orientation Control of ZnO Films Deposited Using Nonequilibrium Atmospheric Pressure N ₂ /O ₂ Plasma. Japanese Journal of Applied Physics, 2013, 52, 01AC03.	0.8	4
122	Electrical Properties of Sol-Gel Derived PbLaZrTiO _x Capacitors with Nonnoble Metal Oxide Top Electrodes. ECS Transactions, 2013, 50, 43-48.	0.3	4
123	Improved reliability properties of (Pb,La)(Zr,Ti)O ₃ ferroelectric capacitors by thin aluminium-doped zinc oxide buffer layer. Electronics Letters, 2014, 50, 799-801.	0.5	4
124	Near-surface structure of polar ZnO surfaces prepared by pulsed laser deposition. Thin Solid Films, 2014, 559, 88-91.	0.8	4
125	Crystallographic polarity effect of ZnO on thin film growth of pentacene. Japanese Journal of Applied Physics, 2017, 56, 04CJ03.	0.8	4
126	Reaction of N,N-dimethylformamide and divalent viologen molecule to generate an organic dopant for molybdenum disulfide. AIP Advances, 2018, 8, 055313.	0.6	4

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127	Quantitative analysis of the direct piezoelectric response of bismuth ferrite films by scanning probe microscopy. <i>Scientific Reports</i> , 2019, 9, 19727.	1.6	4
128	Monolithic Integration of P(VDF-TrFE) Thin Film on CMOS for Wide-band Ultrasonic Transducer Arrays. , 2019, , .		4
129	Change in the defect structure of composition controlled single-phase YbFe ₂ O ₄ epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPB07.	0.8	4
130	Characterization of Direct Piezoelectric Effect in 31 and 33 Modes for Application to Vibration Energy Harvester. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 09ND17.	0.8	4
131	YMnO ₃ and YbMnO ₃ Thin Films for fet type FeRam Application. <i>Materials Research Society Symposia Proceedings</i> , 1999, 574, 237.	0.1	3
132	Effects of spontaneous and piezoelectric polarizations on carrier confinement at the Zn _{0.88} Mn _{0.12} O/ZnO interface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3107-3109.	0.8	3
133	Output power of piezoelectric MEMS vibration energy harvesters under random oscillations. <i>Journal of Physics: Conference Series</i> , 2014, 557, 012101.	0.3	3
134	Novel chemical vapor deposition process of ZnO films using nonequilibrium N ₂ plasma generated near atmospheric pressure with small amount of O ₂ below 1%. <i>Journal of Applied Physics</i> , 2016, 119, 175302.	1.1	3
135	Reliability of the Properties of (Pb,La)(Zr,Ti)O ₃ Capacitors with Non-noble Metal Oxide Electrodes stored in an H ₂ Atmosphere. <i>MRS Advances</i> , 2016, 1, 369-374.	0.5	3
136	Tuning Transition-Metal Dichalcogenide Field-Effect Transistors by Spontaneous Pattern Formation of an Ultrathin Molecular Dopant Film. <i>ACS Nano</i> , 2018, 12, 10123-10129.	7.3	3
137	Electronic Structure Mosaicity of Monolayer Transition Metal Dichalcogenides by Spontaneous Pattern Formation of Donor Molecules. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 15922-15926.	4.0	3
138	Time-resolved simulation of the negative capacitance stage emerging at the ferroelectric/semiconductor hetero-junction. <i>AIP Advances</i> , 2019, 9, 025037.	0.6	3
139	Metallic Transport in Monolayer and Multilayer Molybdenum Disulfides by Molecular Surface Charge Transfer Doping. <i>ACS Applied Materials & Interfaces</i> , 2022, , .	4.0	3
140	Magnetic and dielectric properties of Yb(Mn _{1-x} Al _x)O ₃ thin films. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2008, 55, 1056-1060.	1.7	2
141	Fabrication of robust PbLa(Zr,Ti)O ₃ capacitor structures using insulating oxide encapsulation layers for FeRAM integration. <i>Electronics Letters</i> , 2011, 47, 486.	0.5	2
142	Effects of La substitution for BiFeO ₃ epitaxial thin films. <i>Journal of the Korean Physical Society</i> , 2013, 62, 1069-1072.	0.3	2
143	Fabrication and electrical properties of a (Pb,La)(Zr,Ti)O ₃ capacitor with pulsed laser deposited Sn-doped In ₂ O ₃ bottom electrode on Al ₂ O ₃ (0001). <i>Japanese Journal of Applied Physics</i> , 2017, 56, 07KC02.	0.8	2
144	Origin of the photoinduced current of strongly correlated YMnO ₃ ferroelectric epitaxial films. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 10PB08.	0.8	2

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145	Investigation of piezoelectric energy harvesting from human walking. Journal of Physics: Conference Series, 2018, 1052, 012113.	0.3	2
146	Characterization of piezoelectric MEMS vibration energy harvesters using random vibration. Japanese Journal of Applied Physics, 2018, 57, 11UD10.	0.8	2
147	Fabrication and Characterization of (Ba,La)SnO ₃ Semiconducting Epitaxial Films on (111) and (001) SrTiO ₃ Substrates. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700800.	0.8	2
148	Microenergy harvesting using BiFeO ₃ films. , 2019, , 195-215.		2
149	Strong Photoluminescence Enhancement from Bilayer Molybdenum Disulfide via the Combination of UV Irradiation and Superacid Molecular Treatment. Applied Sciences (Switzerland), 2021, 11, 3530.	1.3	2
150	Supersensitive Ultrasound Probes for Medical Imaging by Piezoelectric MEMS with Complemented Transmitting and Receiving Transducers. , 2020, , .		2
151	Detailed C-V Analysis for YbMnO ₃ /Y ₂ O ₃ /Si Structure. Materials Research Society Symposia Proceedings, 1999, 574, 359.	0.1	1
152	Influence of Antiferromagnetic Ordering on Ferroelectric Polarization Switching of YMnO ₃ Epitaxial Thin Films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
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